FOR HIGH CURRENT DRIVE APPLICATION SILICON NPN EPITAXIAL TYPE

DESCRIPTION

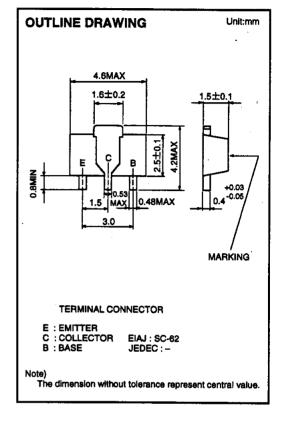
2SC3728 is a silicon NPN epitaxial type transistor. There is a built-in zener diode between collector to emitter.

FEATURE

- ●High hFE hFE=150 to 800
- ●High collector current (Ic=2A)
- ●Low collector to emitter saturation voltage VcE(sat)=0.17V typ(@Ic=1A, Is=50mA)
- ●High collector dissipation Pc=500mW
- Small package for mounting

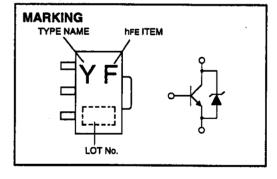
APPLICATION

Camera shutter, solenoid drive circuit.



MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit
Vсво	Collector to Base voltage	20	V
VEBO	Emitter to Base voltage	6	V
VCEO	Collector to Emitter voltage	12	V
Ісм	Peak Collector current	3	Α
lc	Collector current	2	Α
Pc	Collector dissipation(Ta=25℃)	500	mW
Tj	Junction temperature	+150	°C
Tstg	Storage temperature	-55 to +150	ဗ



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
		1 GSL GOTIGIGOTIS	Min	Тур	Max	Office
V(BR)CBO	C to B break down voltage	IC=10 μ A,IE=0	20			٧
V(BR)EBO	E to B break down voltage	IE=10 μ A,Ic=0	6			V
V(BR)CEO	C to E break down voltage	Ic=5mA,RBE=∞	12	14	16	V
Ісво	Collector cut off current	VcB=16V,IE=0			0.1	μΑ
lebo .	Emitter cut off current	VEB=4V,IC=0			0.1	μΑ
hfe *	DC forward current gain	VcE=4V,ic=100mA	150	350	800	_
VCE(sat)	C to E saturation voltage	Ic=1A,is=50mA		0.2	0.35	V
fr	Gain band width product	VcE=2V,IE=-10mA	40	80		MHz
Сор	Collector output capacitance	VcB=10V,IE=0, f=1MHz		28	· · · ·	ρF

^{* :} It shows her classification in right table.

Marking	YE	YF	YG
hFE	150 to 300	250 to 500	400 to 800



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